

## IRFS632-VB Datasheet

### N-Channel 200 V (D-S) MOSFET

#### PRODUCT SUMMARY

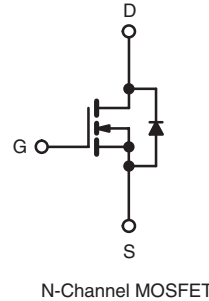
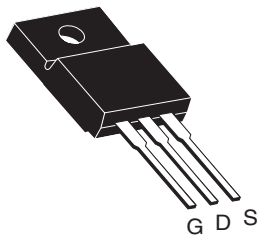
$V_{DS}$ (V)	200	
$R_{DS(on)}$ ( $\Omega$ )	$V_{GS} = 10\text{ V}$	0.265
$Q_g$ (Max.) (nC)	16	
$Q_{gs}$ (nC)	5	
$Q_{gd}$ (nC)	8	
Configuration	Single	

#### FEATURES

- Isolated Package
- High Voltage Isolation = 2.5 kV<sub>RMS</sub> ( $t = 60\text{ s}$ ;  $f = 60\text{ Hz}$ )
- Sink to Lead Creepage Distance = 4.8 mm
- 175 °C Operating Temperature
- Dynamic dV/dt Rating
- Low Thermal Resistance
- Lead (Pb)-free Available



TO-220 FULLPAK



#### ABSOLUTE MAXIMUM RATINGS $T_C = 25\text{ }^\circ\text{C}$ , unless otherwise noted

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			V <sub>DS</sub>	200	V
Gate-Source Voltage			V <sub>GS</sub>	± 20	
Continuous Drain Current	V <sub>GS</sub> at 10 V	T <sub>C</sub> = 25 °C	I <sub>D</sub>	10	A
		T <sub>C</sub> = 100 °C		6.5	
Pulsed Drain Current <sup>a</sup>			I <sub>DM</sub>	32	
Linear Derating Factor				0.24	W/°C
Single Pulse Avalanche Energy <sup>b</sup>			E <sub>AS</sub>	36	mJ
Repetitive Avalanche Current <sup>a</sup>			I <sub>AR</sub>	7.2	A
Repetitive Avalanche Energy <sup>a</sup>			E <sub>AR</sub>	3.7	mJ
Maximum Power Dissipation	T <sub>C</sub> = 25 °C		P <sub>D</sub>	37	W
Peak Diode Recovery dV/dt <sup>c</sup>			dV/dt	5.5	V/ns
Operating Junction and Storage Temperature Range			T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C
Soldering Recommendations (Peak Temperature)		for 10 s		300 <sup>d</sup>	
Mounting Torque	6-32 or M3 screw			10	lbf · in
				1.1	N · m

#### Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = 25\text{ V}$ , starting  $T_J = 25\text{ }^\circ\text{C}$ ,  $L = 1.0\text{ mH}$ ,  $R_G = 25\text{ }\Omega$ ,  $I_{AS} = 7.2\text{ A}$  (see fig. 12).
- $I_{SD} \leq 9.2\text{ A}$ ,  $dI/dt \leq 110\text{ A}/\mu\text{s}$ ,  $V_{DD} \leq V_{DS}$ ,  $T_J \leq 175\text{ }^\circ\text{C}$ .
- 1.6 mm from case.

**THERMAL RESISTANCE RATINGS**

PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	$R_{thJA}$	-	65	°C/W
Maximum Junction-to-Case (Drain)	$R_{thJC}$	-	4.1	

**SPECIFICATIONS**  $T_J = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA		200	-	-	V
V <sub>DS</sub> Temperature Coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	Reference to 25 °C, I <sub>D</sub> = 1 mA		-	0.13	-	V/°C
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA		2.0	-	4.0	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>GS</sub> = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 200 V, V <sub>GS</sub> = 0 V		-	-	25	μA
		V <sub>DS</sub> =160 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 150 °C		-	-	250	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 4.3 A <sup>b</sup>	-	0.265	-	Ω
Forward Transconductance	g <sub>fs</sub>	V <sub>DS</sub> = 50 V, I <sub>D</sub> = 4.3 A <sup>b</sup>		2.3	-	-	S
Dynamic							
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 25 V, f = 1.0 MHz, see fig. 5		-	560	-	pF
Output Capacitance	C <sub>oss</sub>			-	260	-	
Reverse Transfer Capacitance	C <sub>rss</sub>			-	110	-	
Drain to Sink Capacitance	C	f = 1.0 MHz		-	12	-	
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 9.2 A, V <sub>DS</sub> = 80 V, see fig. 6 and 13 <sup>b</sup>	-	-	16	nC
Gate-Source Charge	Q <sub>gs</sub>			-	-	4.4	
Gate-Drain Charge	Q <sub>gd</sub>			-	-	7.7	
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 100 V, I <sub>D</sub> = 9.2 A, R <sub>G</sub> = 18 Ω, R <sub>D</sub> = 5.2 Ω, see fig. 10 <sup>b</sup>		-	8.8	-	ns
Rise Time	t <sub>r</sub>			-	30	-	
Turn-Off Delay Time	t <sub>d(off)</sub>			-	19	-	
Fall Time	t <sub>f</sub>			-	20	-	
Internal Drain Inductance	L <sub>D</sub>	Between lead, 6 mm (0.25") from package and center of die contact		-	4.5	-	nH
Internal Source Inductance	L <sub>S</sub>			-	7.5	-	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I <sub>S</sub>	MOSFET symbol showing the integral reverse p - n junction diode		-	10	-	A
Pulsed Diode Forward Current <sup>a</sup>	I <sub>SM</sub>			-	32	-	
Body Diode Voltage	V <sub>SD</sub>	T <sub>J</sub> = 25 °C, I <sub>S</sub> = 7.2 A, V <sub>GS</sub> = 0 V <sup>b</sup>		-	-	2.5	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C, I <sub>F</sub> = 9.2 A, dI/dt = 100 A/μs <sup>b</sup>		-	130	260	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>			-	0.65	1.3	μC
Forward Turn-On Time	t <sub>on</sub>	Intrinsic turn-on time is negligible (turn-on is dominated by L <sub>S</sub> and L <sub>D</sub> )					

**Notes**

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).  
 b. Pulse width  $\leq 300\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\%$ .

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



Fig. 1 - Typical Output Characteristics,  $T_C = 25\text{ }^{\circ}\text{C}$



Fig. 3 - Typical Transfer Characteristics

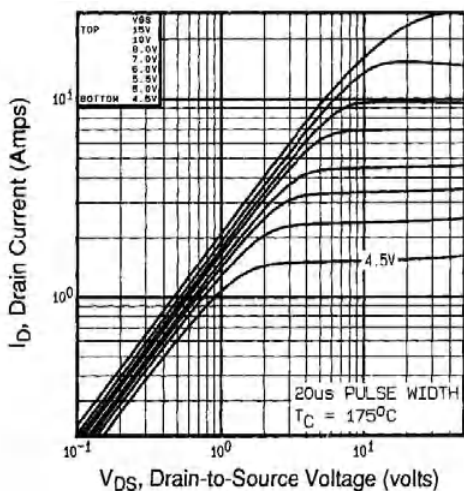


Fig. 2 - Typical Output Characteristics,  $T_C = 175\text{ }^{\circ}\text{C}$

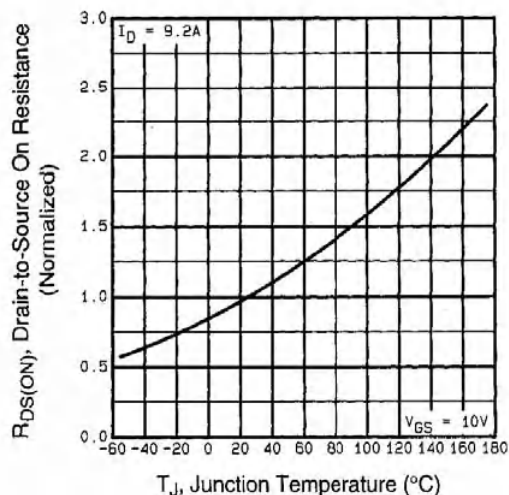


Fig. 4 - Normalized On-Resistance vs. Temperature

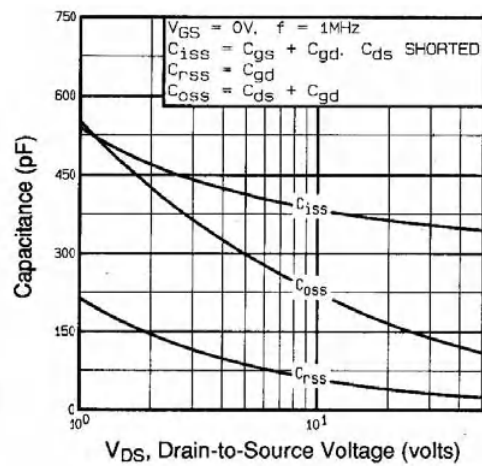


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

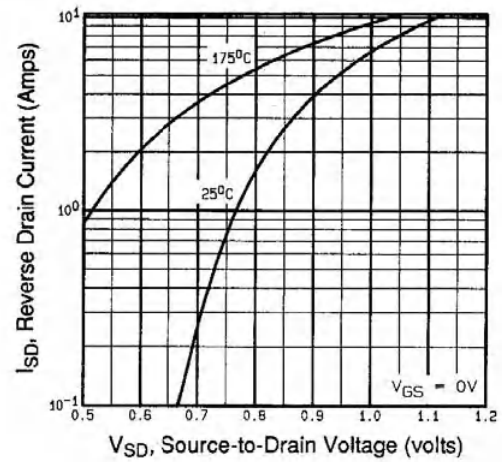


Fig. 7 - Typical Source-Drain Diode Forward Voltage

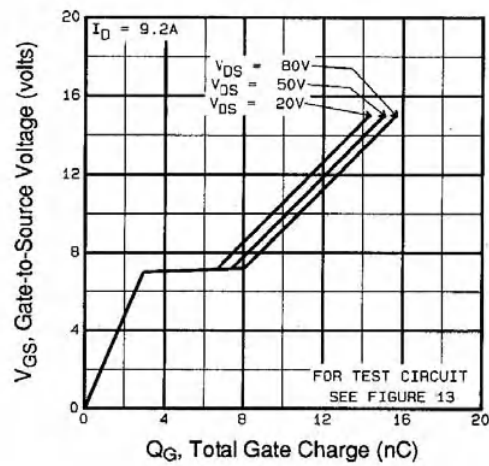


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

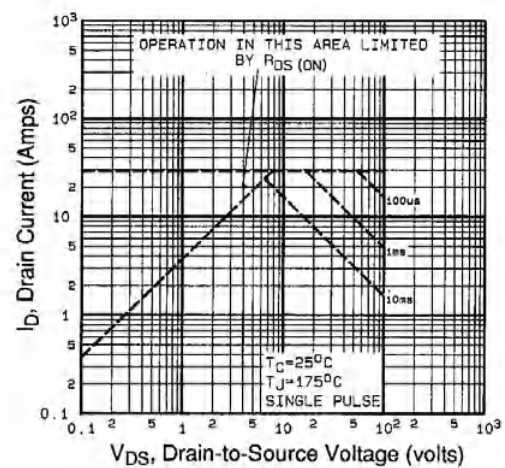


Fig. 5 - Fig. 8 - Maximum Safe Operating Area

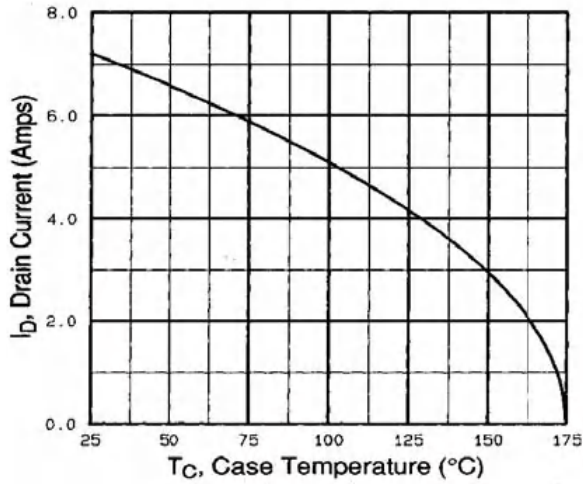


Fig. 9 - Maximum Drain Current vs. Case Temperature



Fig. 10a - Switching Time Test Circuit



Fig. 10b - Switching Time Waveforms



Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

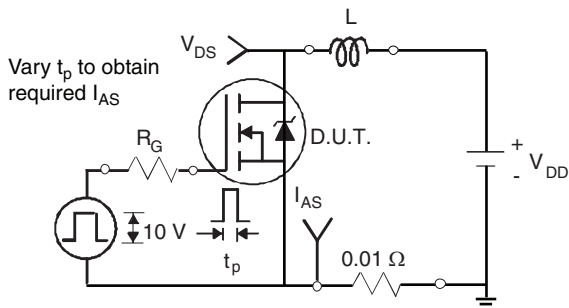


Fig. 12a - Unclamped Inductive Test Circuit

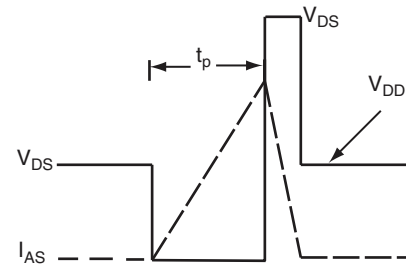


Fig. 12b - Unclamped Inductive Waveforms



Fig. 12c - Maximum Avalanche Energy vs. Drain Current

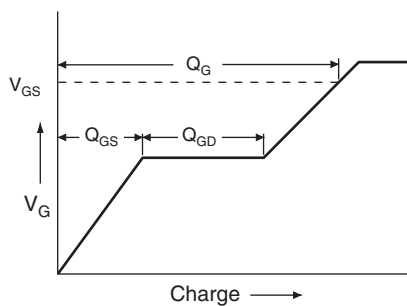


Fig. 13a - Basic Gate Charge Waveform



Fig. 13b - Gate Charge Test Circuit





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